

Title (en)

METHOD FOR TREATING A METAL ELEMENT WITH ION BEAM

Title (de)

VERFAHREN ZUR BEHANDLUNG EINES METALLELEMENTS MIT EINEM IONENSTRAHL

Title (fr)

PROCEDE DE TRAITEMENT D'UNE PARTIE METALLIQUE PAR UN FAISCEAU D'IONS

Publication

**EP 2376668 A1 20111019 (FR)**

Application

**EP 09797120 A 20091130**

Priority

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Abstract (en)

[origin: WO2010063928A1] The present invention relates to a method for treating a metal element subjected to an ion beam, where: - the ions of the beam are selected from among boron, carbon, nitrogen, and oxygen; - the ion acceleration voltage, greater than or equal to 10 kV, and the power of the beam, between 1 W and 10 kW, as well as the ion load per surface unit are selected so as to enable the implantation of ions onto an implantation area with a thickness el of 0.05 µm to 5 µm, and also enable the diffusion of ions into an implantation/diffusion area with a thickness el + eP, of 0.1 µm to 1,000 µm; the temperature TZF of the area of the metal element located under the implantation/diffusion area is less than or equal to a threshold temperature TSD. In this manner, metal surfaces having remarkable mechanical characteristics are advantageously produced.

IPC 8 full level

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